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### (54) SEMICONDUCTOR MEMORY DEVICE

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#### (57) ABSTRACT

A semiconductor memory device according to an embodiment includes a substrate, a source line, word lines, a pillar, and a first member. The first member is provided to penetrate the source line. The first member includes a first portion which is far from the substrate, and a second portion which is near the substrate. The first member includes a first contact and a first insulating film. The first contact is provided to extend from the first portion to the second portion. The first contact is electrically connected to the substrate. The first insulating film insulates the source line from the first contact. The first member includes a stepped portion at a boundary part between the first portion and the second

